

Max-Planck-Institute for Solid State Research



Scientific Facility X-ray Diffraction

Refinement of disordered inorganics



S. Bette, B. Hinrichsen, M. Däntl, M.A. Plass, B.V. Lotsch, T. Takayama, H. Takagi, R.E. Dinnebier

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Max Planck Institute for Solid State Research | Scientific Facility X-ray Diffraction | Heisenbergstr. 1 70569 Stuttgart



How Stacking Faults effect Powder Diffraction Patterns The crystalline state





ideal single crystal:

Definition of crystal: a solid composed of atoms, ions, or molecules arranged in a pattern that is periodic in three dimensions.

real single crystals:



mosaic spread

twinning



crystalline powder:









How Stacking Faults effect Powder Diffraction Patterns Stacking Orders in closed packed Structures





ccp-stacking of metal ions e.g. copper

hcp-stacking of metal ions e.g. magnesium

S. Bette, R.E. Dinnebier *Chapter 2: Understanding stacking disorder in layered functional materials using powder diffraction*, Crystallography in Material Science, DeGruyter (Berlin), 1st edition (2021), 55-92.



How Stacking Faults effect Powder Diffraction Patterns Stacking Orders in closed packed Structures







Microstructural simulations using DIFFaX *The basic concepts*





Fundamental Modes of DIFFaX

explicit: a XRPD pattern from one pre-defined or random sequence of layers and stacking vectors is simulated

recursive: a averaged diffraction pattern is calculated from *all* possible stacking sequences with *transition probability matrix* used as a weighting scheme.

M. M. J. Treacy, J. M. Newsam, M. W. Deem Proc. R. Soc. London Ser. A 1991, 433, 499-520.





Example: 2 % hcp-faults in ccp Cu



 for a large number of layers, the explicit mode creates similar results as the recursive mode!

M. M. J. Treacy, J. M. Newsam, M. W. Deem Proc. R. Soc. London Ser. A 1991, 433, 499-520.









• Identical to the explicit mode in *DIFFaX*

A. A. Coelho, J. S. O. Evans, J. W. Lewis, J. Appl. Cryst. 2016, 49, 1740-1749.





Example: 2 % hcp-faults in ccp Cu



A. A. Coelho, J. S. O. Evans, J. W. Lewis, J. Appl. Cryst. 2016, 49, 1740-1749.



Microstructural refinements using TOPAS *The basic concepts*





1 out of 100 Rietveld refinements using the faultless structure (left) and a 5000 layer supercell (2 % fault probability)

A. A. Coelho, J. S. O. Evans, J. W. Lewis, *J. Appl. Cryst.* 2016, *49*, 1740-1749.
C. M. Ainsworth, J. W. Lewis, C.-H. Wang, A. A. Coelho, H. E. Johnston, H. E. A. Brand, J. S. O. Evans, *Chemistry of Materials* 2016, *28*, 3184-3195.





How can we utilize these software features for getting a better understanding of our materials?

- 1. Honeycomb Compounds
 - a) $H_3LiIr_2O_6$, $Ag_3Li(Ir/Ru)_2O_6$ – derivation of the layer constitution
 - b) $Li_3HoBr_{6-x}I_x$ intra- vs. interlayer disorder
- 2. Brucite-type materials
 - a) NCA precursors optimization of multiple parameters
- 3. Excursus into thin films
 - a) spin coated $H_3Sb_3P_3O_{14}$ thin films
- 4. Conclusions and Outlook















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- On Ru • Li • Ag • 0



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- synthesis by cation exchange via soft chemistry
- heavy stacking faulting of the sheets indicated by anisotropic peak broadening in the XRPD pattern



5

6

8

20/ ° (Ag-K ,)

9

10

11

H. Takagi





















Microstructural refinements using TOPAS *Tackling Problems: Derivation of the layer constitution*



• layer constitution of the ideal structure:

honeycomb layer







 stacking order of the ideal structure:



• alternative stacking order of the ideal structure:









Ir/Ru
 bottom layer: bottom side O; top layer: top side O
 bottom layer: top side O; top layer: bottom side O
 O2 sites indicating the alternative stacking vectors







● Ir/Ru ● bottom layer: bottom side O; top layer: top side O ● O1 sites indicating the stacking vectors

bottom layer: top side O; top layer: bottom side O







O Ir/Ru ● bottom layer: bottom side O; top layer: top side O ● O1 sites indicating the stacking vectors

bottom layer: top side O; top layer: bottom side O

O2 sites indicating the alternative stacking vectors







O Ir/Ru ● bottom layer: bottom side O; top layer: top side O ● O1 sites indicating the stacking vectors

bottom layer: top side O; top layer: bottom side O







bottom layer: top side O; top layer: bottom side O
 O2 sites indicating the alternative stacking vectors







Ir/Ru
 bottom layer: bottom side O; top layer: top side O
 bottom layer: top side O; top layer: bottom side O
 O2 sites indicating the alternative stacking vectors



Honeycomb Compounds - H₃Lilr₂O₆, Ag₃Li(lr/Ru)₂O₆ Creation of a transition probability matrix





from↓/ to→	O1-H-O1	O1-H-O2	O1-H-O2	O1-H-O2	O1-H-O2
	Contact	contact-1	contact-2	contact-3	contact-4
O1-H-O1	P ₁₁ ,	P ₁₂ ,	P ₁₃ ,	P ₁₄ ,	P ₁₅ ,
contact	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	P ₂₁ ,	P ₂₂ ,	P ₂₃ ,	P ₂₄ ,	P ₂₅ ,
contact-1	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	P ₃₁ ,	P ₃₂ ,	P ₃₃ ,	P ₃₄ ,	P ₃₅ ,
contact-2	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	P ₄₁ ,	P ₄₂ ,	P ₄₃ ,	P ₄₄ ,	P ₄₅ ,
contact-3	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	P ₅₁ ,	P ₅₂ ,	P ₅₃ ,	P ₅₄ ,	P ₅₅ ,
contact-4	S1	S2-1	S2-2	S2-3	S2-4



Honeycomb Compounds - H₃Lilr₂O₆, Ag₃Li(lr/Ru)₂O₆ Parameter reduction



assumption: all alternative stacking orders are equally favorable

global fault probability: P_x



from↓/ to→	O1-H-O1	O1-H-O2	O1-H-O2	O1-H-O2	O1-H-O2
	Contact	contact-1	contact-2	contact-3	contact-4
O1-H-O1	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25· <mark>P_x,</mark>	0.25∙ <mark>P</mark> _x ,
contact	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25· <mark>P_x,</mark>	0.25· <mark>P_x,</mark>	0.25 [.] <mark>P</mark> _x ,
contact-1	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25· <mark>P_x,</mark>	0.25· <mark>P_x,</mark>	0.25⁺ <mark>P</mark> _x ,
contact-2	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25· <mark>P_x,</mark>	0.25∙ <mark>P</mark> _x ,
contact-3	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25 [.] P _x ,	0.25 [.]	0.25 [.] <mark>P</mark> _x ,
contact-4	S1	S2-1	S2-2		S2-4



















Honeycomb Compounds - H₃Lilr₂O₆, Ag₃Li(lr/Ru)₂O₆ Parameter opitmization



from↓/ to→	O1-H-O1	O1-H-O2	O1-H-O2	O1-H-O2	O1-H-O2
	Contact	contact-1	contact-2	contact-3	contact-4
O1-H-O1	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,
contact	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,
contact-1	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25· <mark>P_x,</mark>	0.25∙ <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,
contact-2	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> _x ,	0.25 [.] <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,
contact-3	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	1- <mark>P</mark> x,	0.25 [.] <mark>P</mark> _x ,	0.25∙ <mark>P</mark> _x ,	0.25· <mark>P_x,</mark>	0.25∙ <mark>P</mark> _x ,
contact-4	S1	S2-1	S2-2	S2-3	S2-4





c-direction

Honeycomb Compounds - H₃Lilr₂O₆, Ag₃Li(lr/Ru)₂O₆ Interpretation of the result



from //	O1-H-				
n om _↓ /	01	01-8-02	01-1-02	01-1-02	01-1-02
to→	Contact	contact-1	contact-2	contact-3	contact-4
01-H-01	0.24,	0.19 ,	0.19,	0.19 ,	0.19 ,
contact	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	0.24,	0.19 ,	0.19,	0.19 ,	0.19 ,
contact-1	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	0.24,	0.19 ,	0.19 ,	0.19 ,	0.19 ,
contact-2	S1	S2-1	S2-2	S2-3	S2-4
O1-H-O2	0.24,	0.19 ,	0.19 ,	0.19 ,	0.19 ,
contact-3	S1	S2-1	S2-2	S2-3	S2-4
01-H-O2	0.24,	0.19 ,	0.19 ,	0.19 ,	0.19 ,
contact-4	S1	S2-1	S2-2	S2-3	S2-4

S1 S2-1 S2-2 S2-3 S2-4 *stacking order*

 ➢ extension of the coherently stacked sections
 ≤ 2.4 nm in *c*-direction!





Honeycomb Compounds - H₃Lilr₂O₆, Ag₃Li(lr/Ru)₂O₆ Transfer to related systems



$Ag_{3}Lilr_{2}O_{6}/Ag_{3}LiRu_{2}O_{6}$



Bette, S., Takayama, T., Duppel, V., Poulain, A., Takagi, H, Dinnebier, R.E. Dalton Trans. 2019, 48, 9250 – 9259.









M.A. Plass B.V. Lotsch



Plass, M.A., Bette, S., Dinnebier, R.E., Lotsch, B. Chem. Mater. 2022, 34, 3227-3235.



Heating of Li₃Hol₆:



- considerable thermal expansion
- by heating 110, 111, 021 appear from diffuse scattering
- further heating leads a reduction of the intensity of the 020, 110, 111 and 021 reflection



Honeycomb Compounds - Li₃HoBr_{6-x}l_x intra- vs. interlayer disorder



Heating of Li₃Hol₆: intra layer disorder 350 stacking fault disorder 131 202 001 fautless 300 331/133 020 250 Intensity^{0.5} 30 °C 100 °C 200 Intensity^{0.5} 200 °C 150 300 °C 001 110 111 400 °C 021 100 500 °C 50 400 °C 300 °C 200 °C 9 5 6 8 100 °C 20/ ° (Ag-K,1) 30 °C 20 25 10 15 30 35 20/ ° (Ag-K at)

- considerable thermal expansion
- by heating 110, 111, 021 appear from diffuse scattering
- further heating leads a reduction of the intensity of the 020, 110, 111 and 021 reflection



Honeycomb Compounds - Li₃HoBr_{6-x}l_x intra- vs. interlayer disorder







- considerable thermal expansion
- by heating 110, 111, 021 appear from diffuse scattering
- further heating leads a reduction of the intensity of the 020, 110, 111 and 021 reflection







The impact of disorder on ion conductivity:



• intralayer cation disorder rather impacts ion conductivity than interlayer stacking fault disorder

Plass, M.A., Bette, S., Dinnebier, R.E., Lotsch, B. Chem. Mater. 2022, in press.





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🗅 Ru 🔍 Li 🔍 Act 🎍 O





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NCA and NCM Battery material precursor "(Ni, Co, Al/Mn)(OH)₂ compounds" stacking sequence: а a a a ○ Ni/Co/Al ● O

- layered double hydroxide (LDH) phase
- cation sublattice (NCA): 90 % Ni, 5 % Co, 5 % Al

4.64 Å

- cation sublattice (NCM): 85 % Ni, 10 % Co, 5 % Mn
- brucite-type lattice
- space group $P\overline{3}m1$

BASF



B. Hinrichsen

Bette, S., Hinrichsen, B., Pfister, D., Dinnebier, R.E. J. Appl. Cryst. 2020, 53, 76-87.



Brucite-type materials

NCA precursors – optimization of multiple parameters









Bette, S., Hinrichsen, B., Pfister, D., Dinnebier, R.E. J. Appl. Cryst. 2020, 53, 76-87.



Defining possible transitions



Bette, S., Hinrichsen, B., Pfister, D., Dinnebier, R.E. J. Appl. Cryst. 2020, 53, 76-87.





Building a microstructural model

to→	C6-stacking	C19-	3R-	Inter-
/from↓		stacking	stacking	calation
C6-	1-P _x -P _y -P _{car}	P _x ,	P _y ,	P _{car} ,
stacking	<mark>S1</mark>	S2	S3	S4
C19-	1-P _x -P _y -P _{car}	P _x ,	P _y ,	P _{car} ,
stacking	<mark>S1</mark>	<mark>S2</mark>	S3	S4
3R-	1-P _x -P _y -P _{car}	P _x ,	P _y ,	P _{car} ,
stacking	<mark>S1</mark>	<mark>S2</mark>	S3	S4
Inter- calation	0	0	0	1, S5





Problem 2: optimization of the transition probabilities



Coelho, A.A. *J. Appl. Cryst.* **2018**, 51, 210.I Bette, S. et al. *Dalton Trans.* **2019**, 48, 9250.I Bette, S. et al. *J. Appl. Cryst.* **2020**, 53, 76-87.



Problem 2: optimization of the transition probabilities



Coelho, A.A. *J. Appl. Cryst.* **2018**, 51, 210.1 Bette, S. et al. *Dalton Trans.* **2019**, 48, 9250.1 Bette, S. et al. *J. Appl. Cryst.* **2020**, 53, 76-87.



Problem 2: optimization of the transition probabilities



global minimum within $0.10 \le P_x \le 0.24 \cup 0.00 \le P_y \le 0.19$

global minimum within $0.10 \le P_x \le 0.24 \cup 0.04 \le P_{car} \le 0.09$

Coelho, A.A. *J. Appl. Cryst.* **2018**, 51, 210.I Bette, S. et al. *Dalton Trans.* **2019**, 48, 9250.I Bette, S. et al. *J. Appl. Cryst.* **2020**, 53, 76-87.



Problem 2: optimization of the transition probabilities



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Problem 2: optimization of the transition probabilities



Bette, S., Hinrichsen, B., Pfister, D., Dinnebier, R.E. J. Appl. Cryst. 2020, 53, 76-87.





Problem 2: optimization of the transition probabilities

Scattering of the results



Minimum at: P_x = 0.15(1), P_y = 0.06(1), P_{car} = 0.07(1), Rwp = 6.4 %

Bette, S., Hinrichsen, B., Pfister, D., Dinnebier, R.E. J. Appl. Cryst. 2020, 53, 76-87.





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🗅 Ru 🔍 li 🔍 Act 🎍 O







3D-networks and thin films spin coated H₃Sb₃P₃O₁₄ thin films







M. Däntl B.V. Lotsch





 home built cell, amine dissolved in EtOH, intercalation via gas transport





3D-networks and thin films

spin coated $H_3Sb_3P_3O_{14}$ thin films



- intercalation of EtOH, amin or of both EtOH and amin possible
- only the interlayer distance of the prestine amin (h1) was known







spin coated $H_3Sb_3P_3O_{14}$ thin films





Däntl, M., Maschita, J., Wochner, P., Jiménez-Solano, A.m Vignolo-Gonzalez, H., Putzky, D., Dinnebier, R, E., Bette, S., Lotsch, B.V. *in preparation*



3D-networks and thin films

spin coated $H_3Sb_3P_3O_{14}$ thin films







- Amine Si Wafer EtOH H₃Sb₃P₂O₁₄ layer
- a) initally EtOH is present from spin coating
- b) deintercalation of EtOH by evaporation (EtOH)
- c) injection amin solution (in EtOH) → EtOH saturation of the atmosphere → EtOH reinterclation
- d) intercalation of amin in EtOH intercalated layers
- e) extrusion of EtOH from double intercalated layers
- f) final state

Däntl, M., Maschita, J., Wochner, P., Jiménez-Solano, A.m Vignolo-Gonzalez, H., Putzky, D., Dinnebier, R, E., Bette, S., Lotsch, B.V. *in preparation*



 qualitative and quantitative information on disorder like stacking faults become more and more important to understand *crystal structures, properties* and *chemical*[®] *processes*







InRe Obstitum layer: bottom side O: top layer: too wide O OI stars indicating the stacking vectors Obstitum layer: top side O: top layer: bottom side O OO stars indicating the alternative stacking vectors



- qualitative and quantitative information on disorder like stacking faults become more and more important to understand *crystal structures, properties* and *chemical*[™] *processes*







• in an ideal world:



the magic black box



output







qualitative and quantitative information on disorder like stacking faults become more and more important to understand crystal structures, properties and chemical processes









in an ideal world:





the magic





 qualitative and quantitative information on disorder like stacking faults become more and more important to understand *crystal structures, properties* and *chemical processes*









- iRu @bottom layer: bottom side O: top layer: too side O: @O1 stas indicating the stacking rectors @bottom layer: top side O: top layer: bottom side O: @O2 stas indicating the alternative stacking vectors
- in an ideal world: the magic black box 0000 40000 press 30000 30000 y_{obs} - y_{calc} button output 20000 **월** 20000 Intensity/ cour We are 0000 10000 getting 10000 closer! -10000 Rwp = 6.4 % Rwp = 32.4 % 20000 20000 40 10 15 20 30 40 2 0/ ° (Mo-K ...) 2 0/ ° (Mo-K .) the real world: derive adapt already layer constitution, known routines stacking vectors, ...



Acknowledgement









Max-Planck-Institute for Solid State Research





Reviewers of: *J. Appl. Cryst.* **2020**, 53, 76-87.







A.A. Coelho







Thank you for your attention!